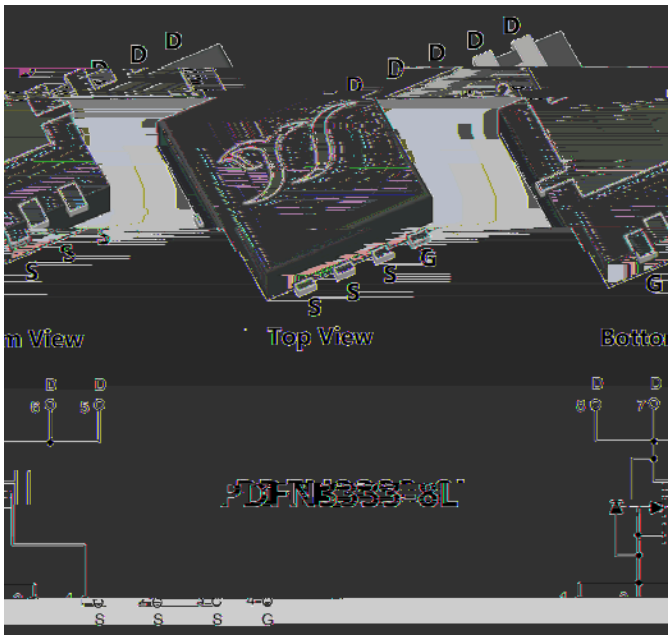
ŏ 100% V



DS Tested

General Description

● Excellent package fo

					Unit
Drain-source Voltage			V_{DS}	40	V
Gate-source Voltage			V_{GS}	±20	V
Continuous Drain Current (Note 1,2)	Steady-State	T_A=25 , V_{GS}= 10V	I_D	16.9	A
		T_A=100 , V_{GS}= 10V		11.9	
Continuous Drain Current (Note 1,3)	Steady-State	T_C=25 , V_{GS}= 10V		75	
		T_C =100 , V_{GS}= 10V		53	
Pulsed Drain Current	T_C=25 , t =100µs		I_{DM}	250	A
Avalanche energy	V_G=10V, R_G=25Ω, L=0.5mH, IAS=14.7A		EAS	54	mJ
Total Power Dissipation (Note 1,2)	Steady-State	T_A=25	P_D	2.3	W
		T_A=100		1.1	

	J ,T_{STG}	-55 +175	

■Thermal resistance

Parameter	Symbol	Typ	

			MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJQ4D8G04HQ	F1	Q4D8G04	5000	10000	100000	13“ reel

YJQ4D8G04HQ

■Typical Electrical and Thermal Characteristics Diagrams

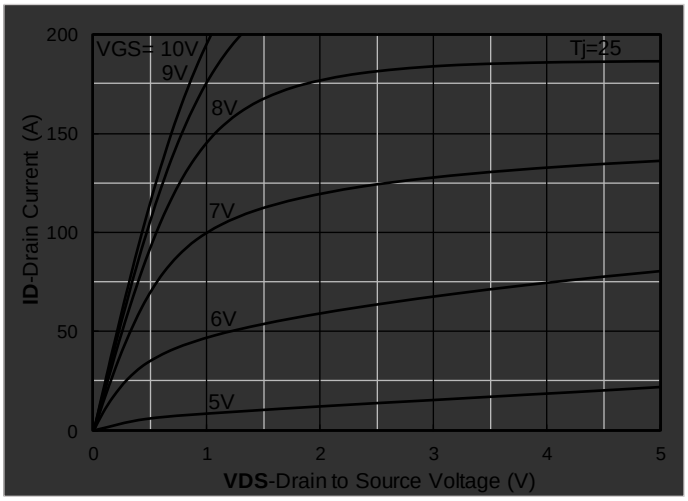


Figure 1. Output Characteristics

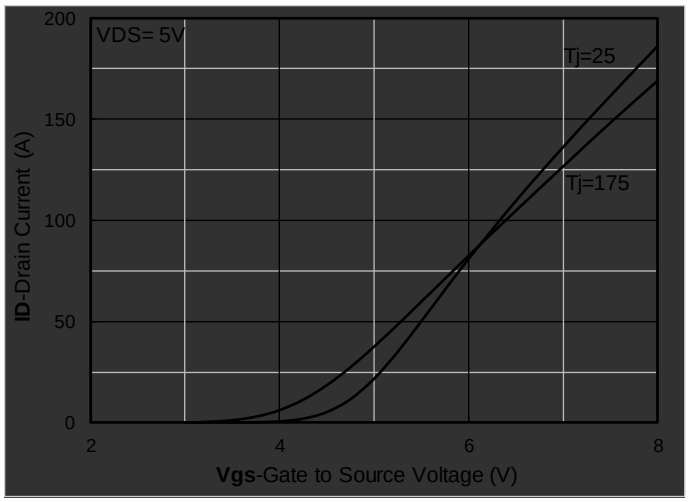


Figure 2. Transfer Characteristics

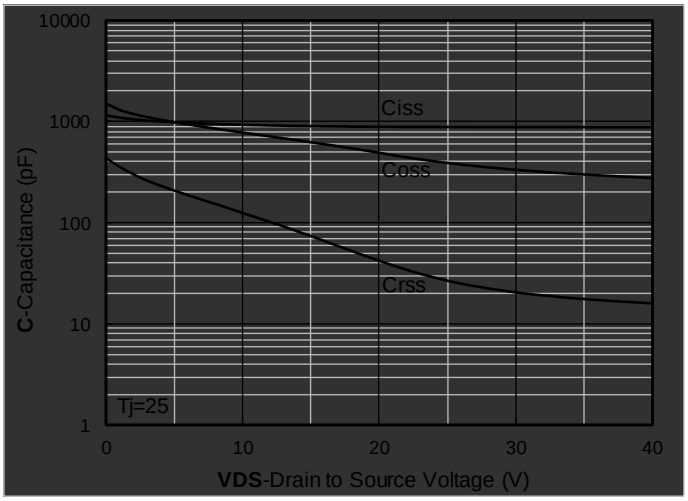


Figure 3. Capacitance Characteristics

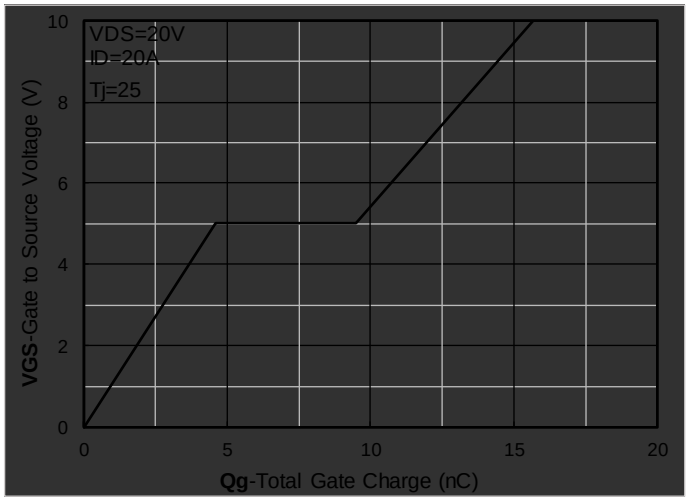


Figure 4. Gate Charge

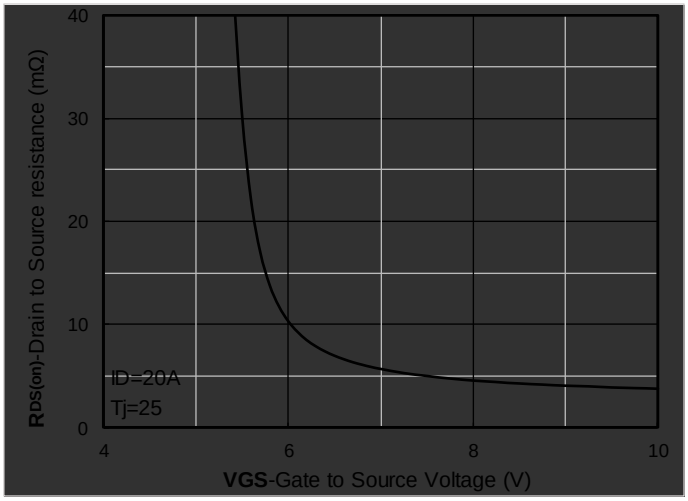


Figure 5. On-Resistance vs Gate to Source Voltage

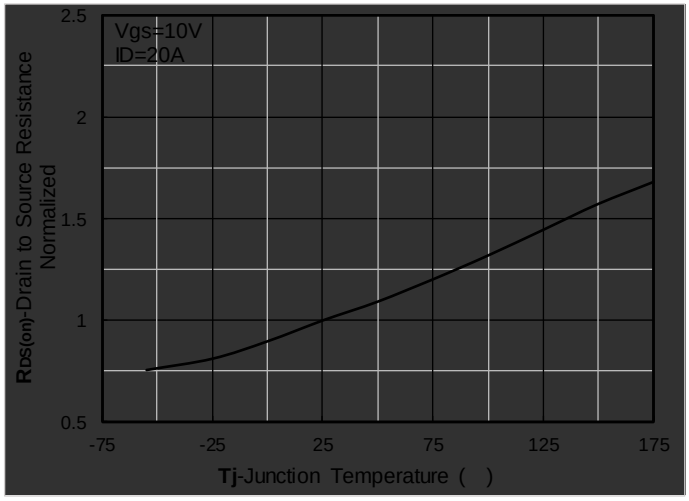


Figure 6. Normalized On-Resistance

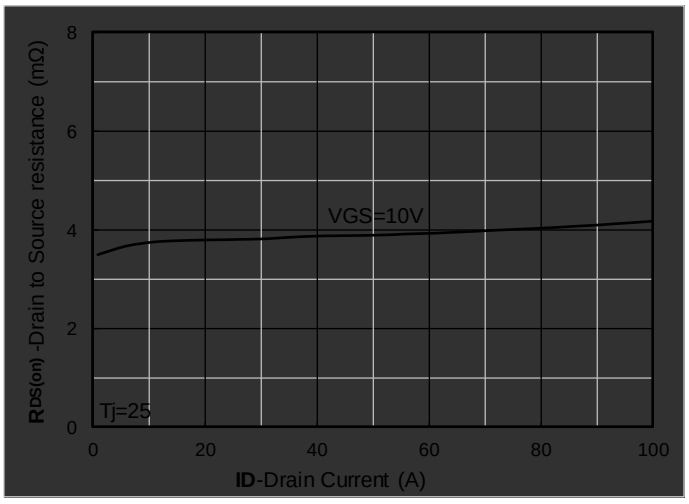


Figure 7. $R_{DS(on)}$ VS Drain Current

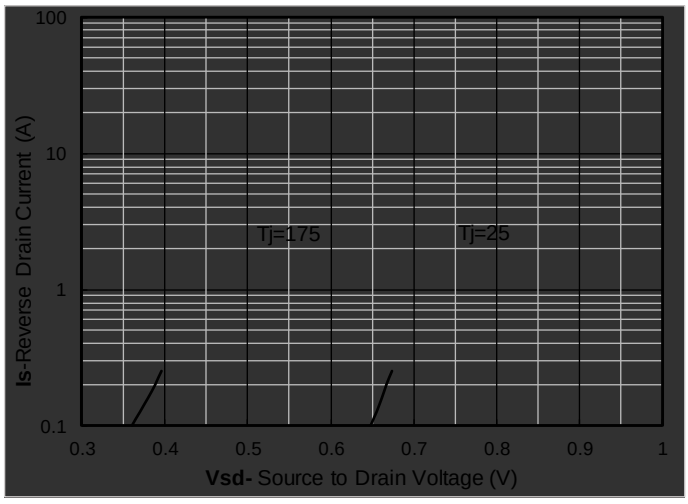


Figure 8. Forward characteristics of reverse diode

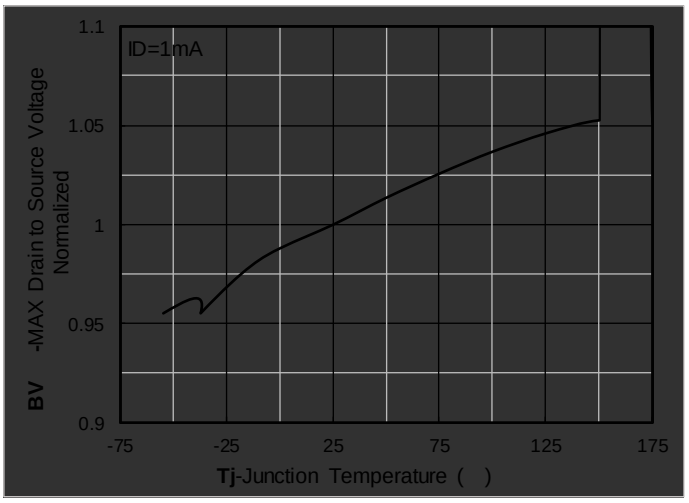


Figure 9. Normalized breakdown voltage

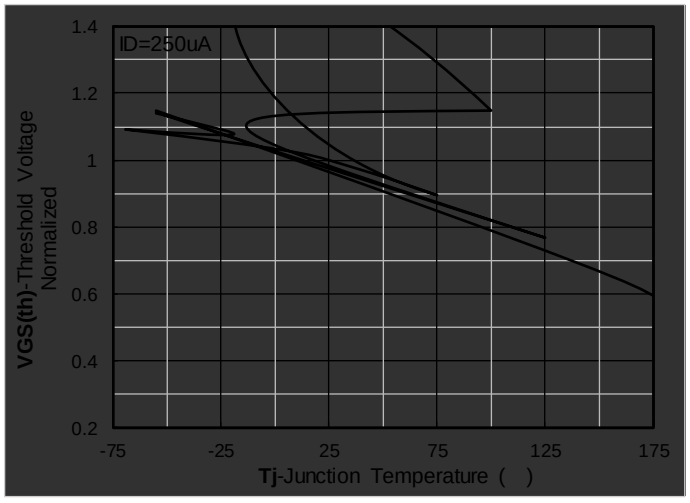


Figure 10. Normalized Threshold voltage

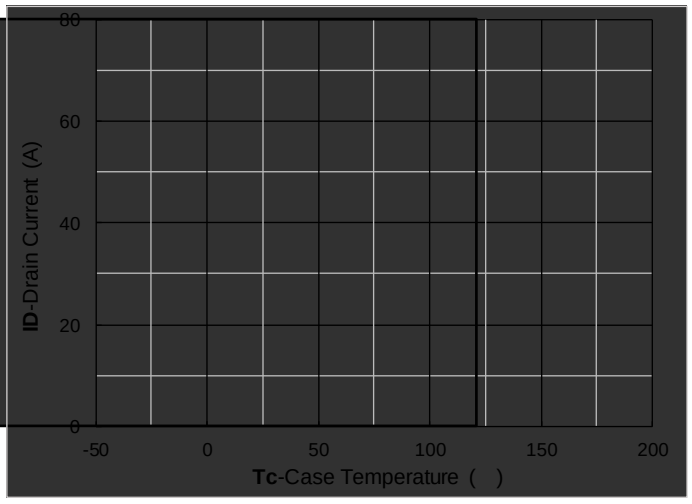


Figure 11. Current dissipation

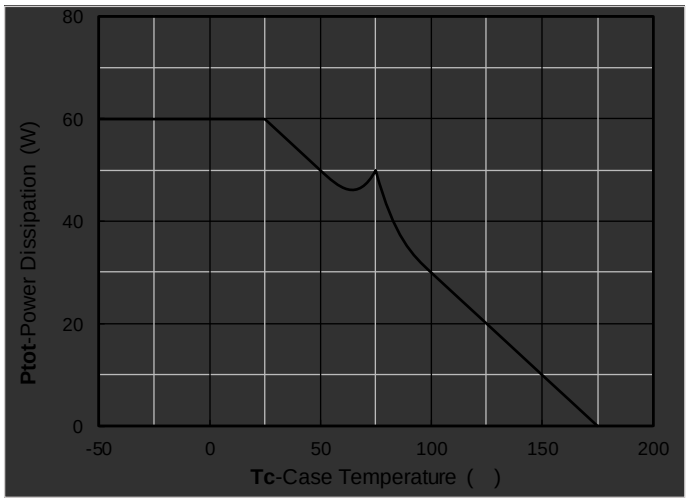
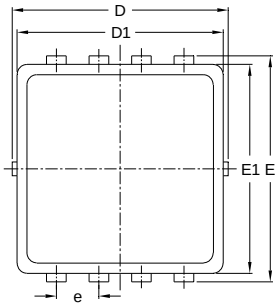
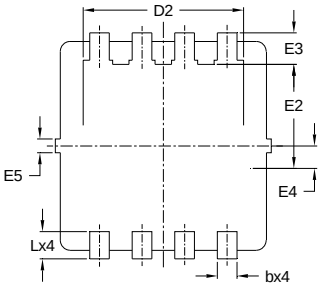


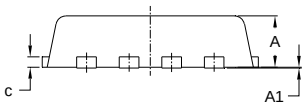
Figure 12. Power dissipation


0.000
Square

■ PDFN3333-8L-B-0.75MM Package information







UNIT mm

DIMENSIONS				
SYMBOL	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.028	0.033	0.700	0.850
A1	0.000	0.002	0.000	0.050
b	0.008	0.016	0.200	0.400
c	0.004	0.010	0.100	0.250
D	0.124	0.136	3.150	3.450
D1	0.118	0.130	3.000	3.300
D2	0.089	0.104	2.250	2.650
E	0.124	0.136	3.150	3.450
E1	0.114	0.126	2.900	3.200
E2	0.052	0.068	1.320	1.720
E3	0.011	0.026	0.280	0.650
E4	0.013 REF		0.330 REF	
E5	0.008 REF		0.200 REF	
e	0.026 BSC		0.650 BSC	
L	0.012	0.020	0.300	0.500

NOTE:
1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.